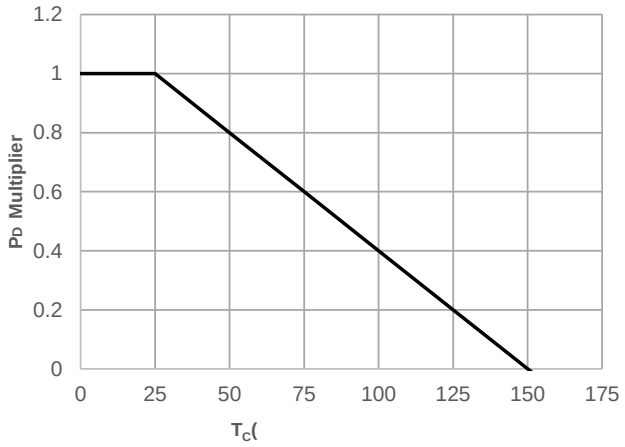
	Value	Unit
	-30	V
	-1.7	V
	-57	A
	7.9	mΩ
	11.7	m

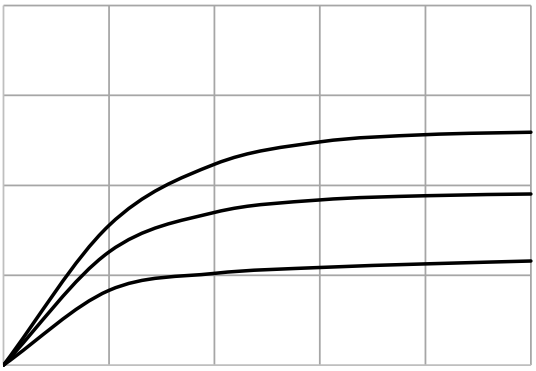
Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Min.

Typical Performance Characteristics



Typical Performance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

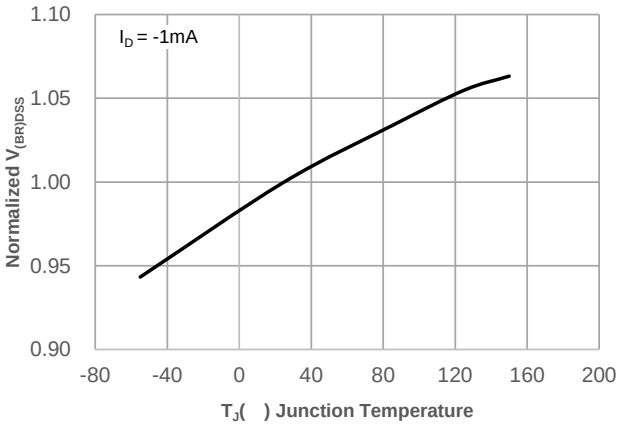
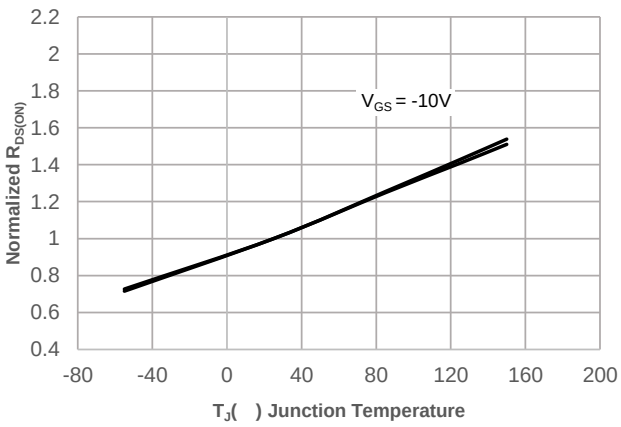


Figure 12: Normalized on Resistance vs. Junction Temperature



Test Circuit

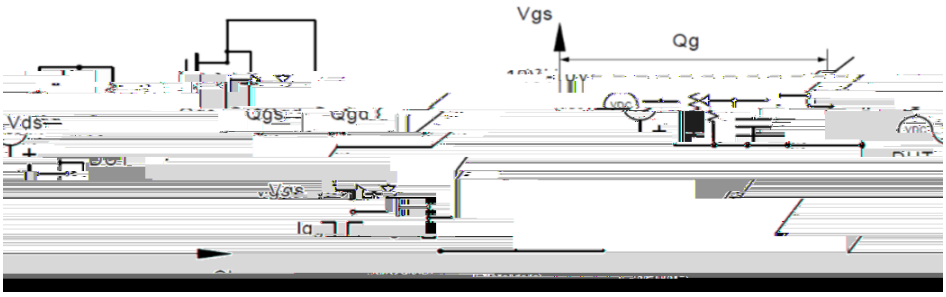


Figure 1: Gate Charge Test Circuit & Waveform

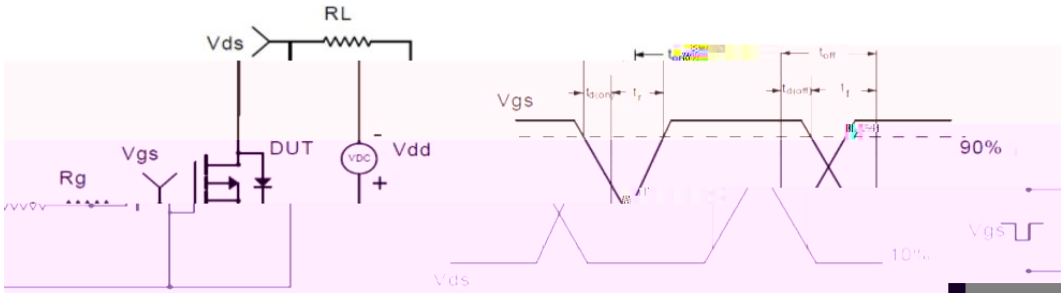


Figure 2: Resistive Switching Test Circuit & Waveform

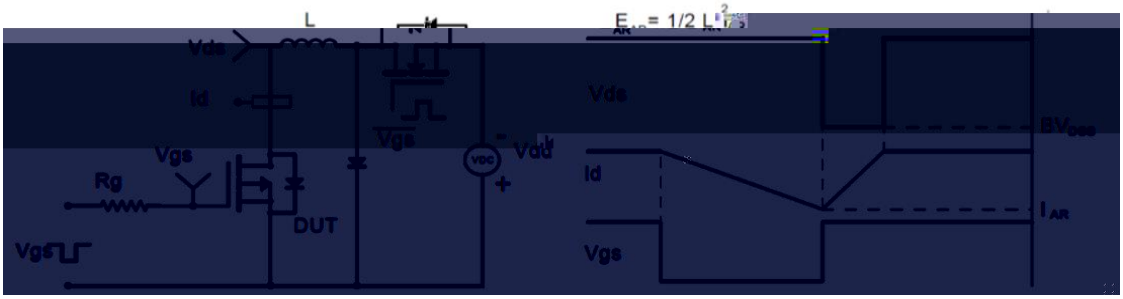


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

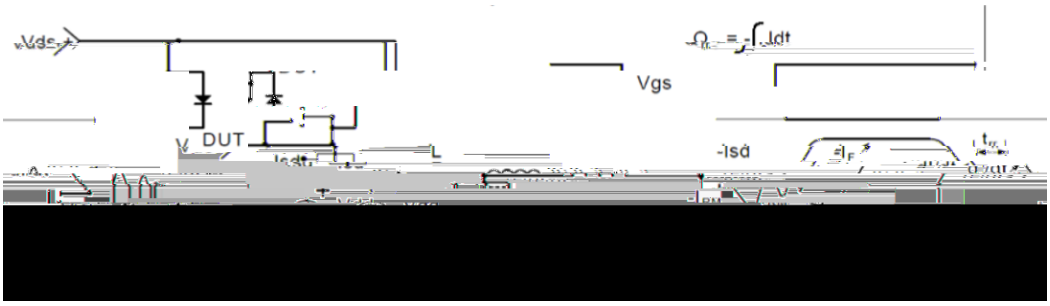
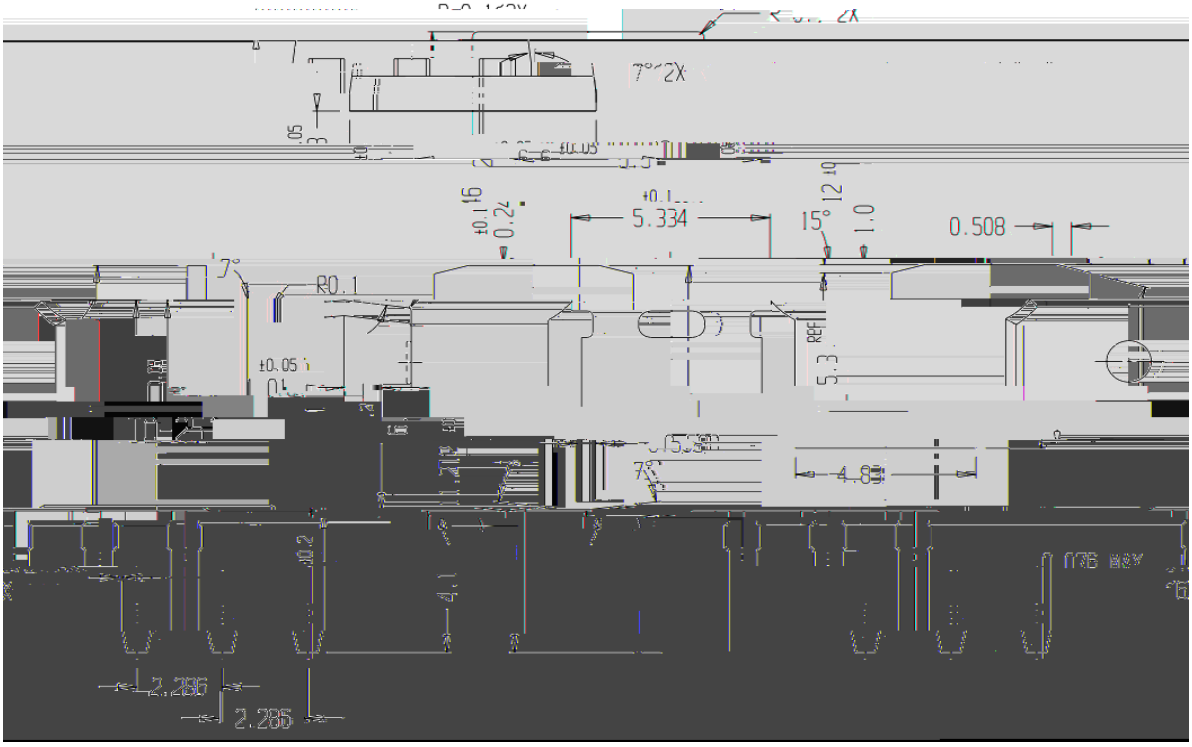


Figure 4: Diode Recovery Test Circuit & Waveform

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Package Mechanical Data(TO-251-3L)



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